



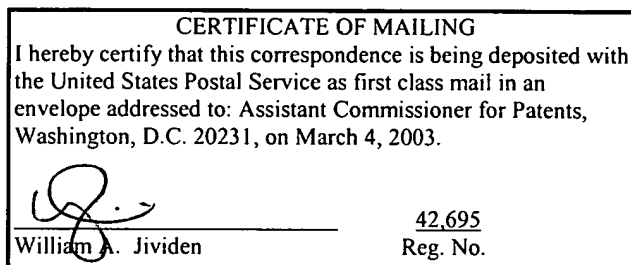
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#8/a
3/18/03
Shm TH

Application of

Applicants : Trivedi et al.
Serial No. : 09/808,864
Confirm. No. : 5568
Filed : March 15, 2001
Title : **SUPPRESSION OF CROSS DIFFUSION AND GATE
DEPLETION**
Docket No. : MIO 0079 PA
Examiner : Foong, Suk-San
Art Unit : 2823

Assistant Commissioner for Patents
Washington, D.C. 20231



Sir:

AMENDMENT

This paper is being filed in response to the Office Action of February 18, 2003. Reconsideration of the present application is respectfully requested in light of the amendments and remarks below.

Attached hereto as an Appendix is a marked-up reproduction of the above-amended sections of the specification, abstract, and claims, wherein additions are underscored and deletions are stricken.

RECEIVED
MAR 17 2003
TECHNOLOGY CENTER 2800

IN THE SPECIFICATION

In the specification, be amend as the following:

Please replace the paragraph on page 1, starting at line 7, with:

--Integrated circuit devices commonly employ a laminar or polysilicide structure composed of a polycrystalline silicon film and an overlying film of a metal, metal silicide, or metal nitride. In many cases, the polycrystalline silicon film comprises an N+

03/14/2003 SDENB081 00000078 09808864

01 FC:1202

72.00 OP